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Realization and characterization of vertical PIN diode on 100 diamond

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► **To cite this version:**

Florent Sevely, Josiane Tasselli, Karine Isoird, Luong Viêt Phung, Camille Sonnevile, et al.. Realization and characterization of vertical PIN diode on 100 diamond. 33rd International Conference on Diamond and Carbon Materials, Sep 2023, Palma, Spain. , 2023. hal-04193251

HAL Id: hal-04193251

<https://laas.hal.science/hal-04193251v1>

Submitted on 1 Sep 2023

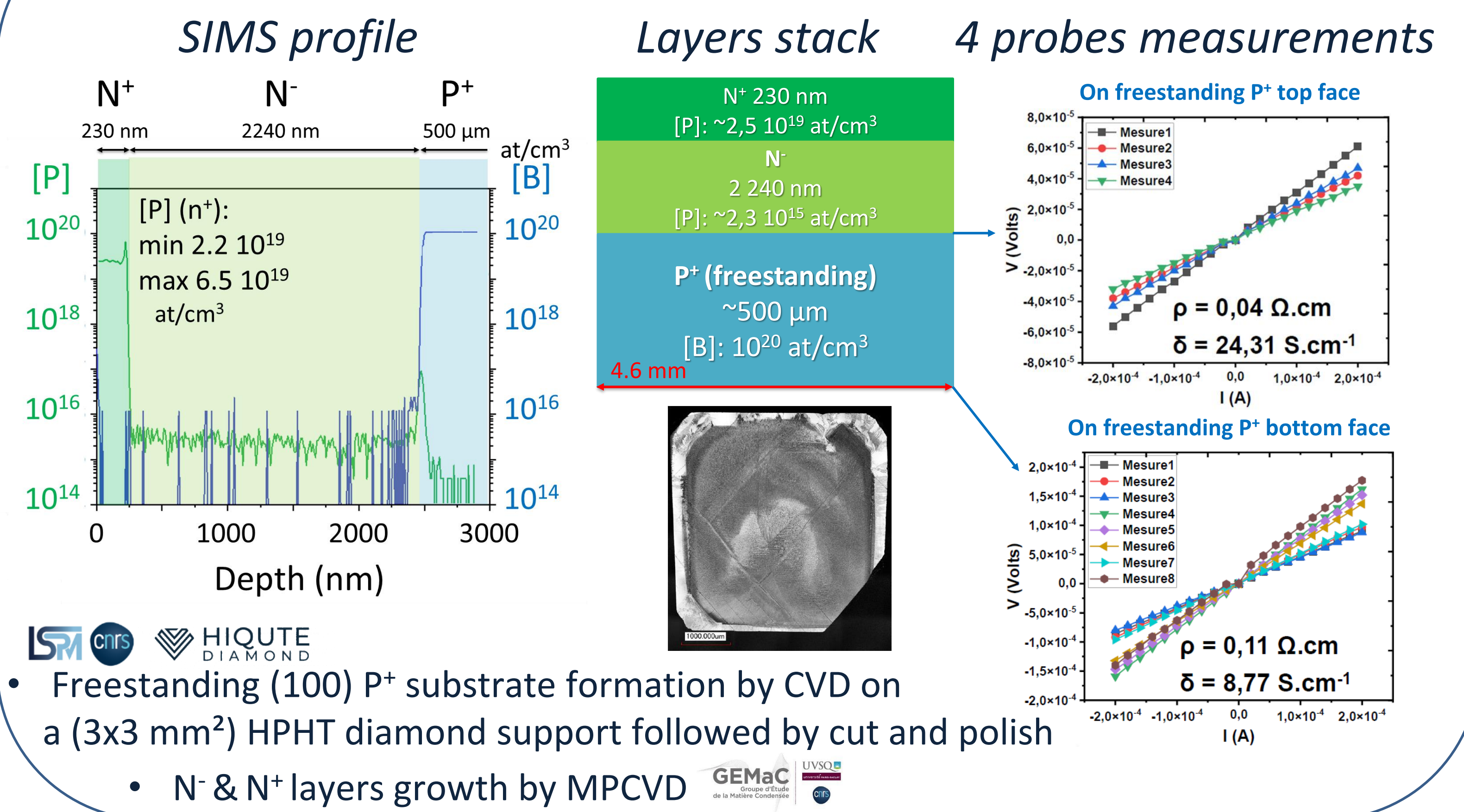
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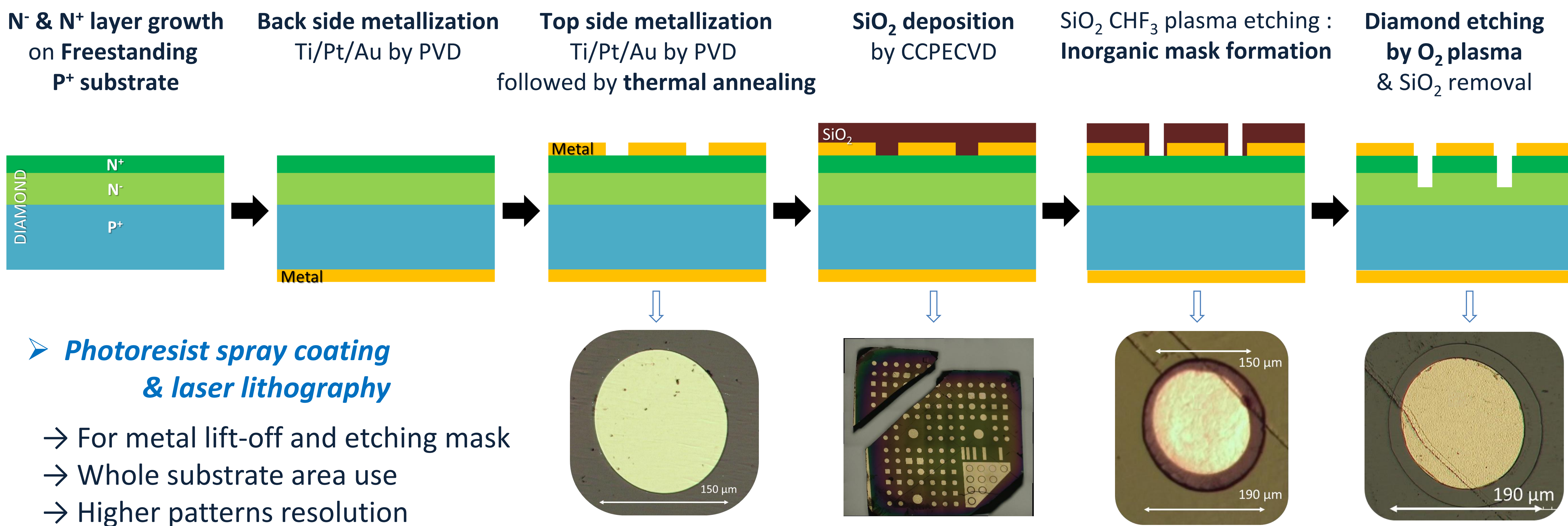
Objectives

- Fabrication of the 1st high voltage vertical (100) PIN diodes on diamond
- Manufacture of (100) freestanding heavily boron doped layer (P⁺) with low density of dislocations
- Optimisation of (100) N⁺ layer growth with low surface roughness.
- Mastery of microfabrication technological steps

PIN layers stack

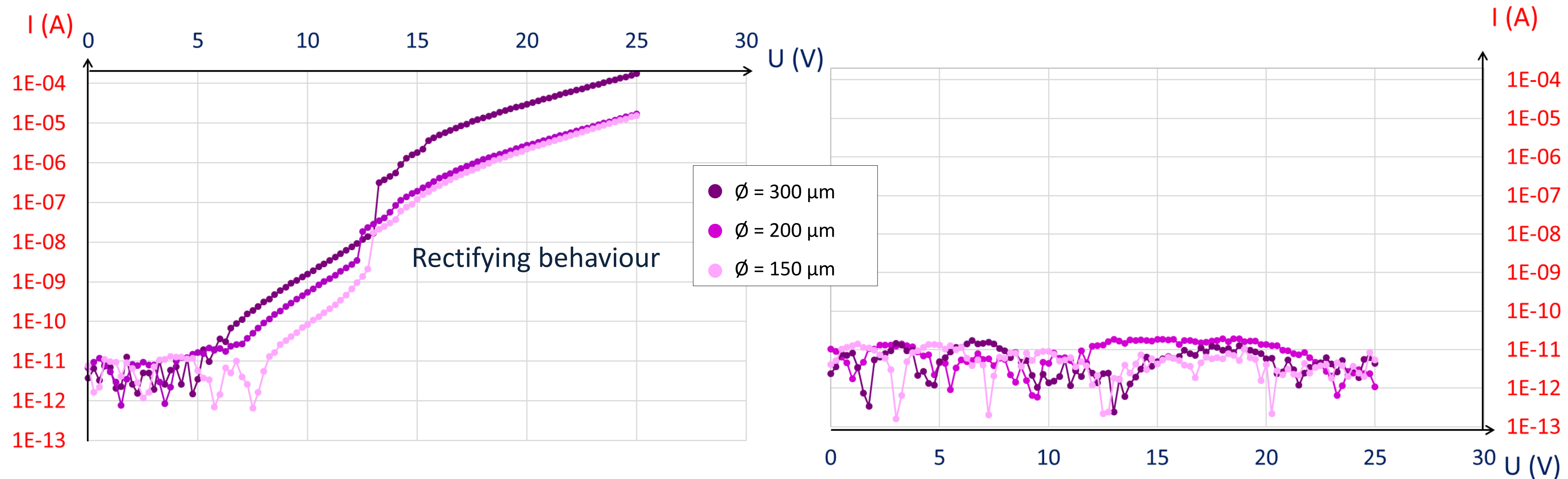


Technological key steps



Electrical characterizations

➤ Forward & Reverse I(V) measurements for 3 types of circular diodes

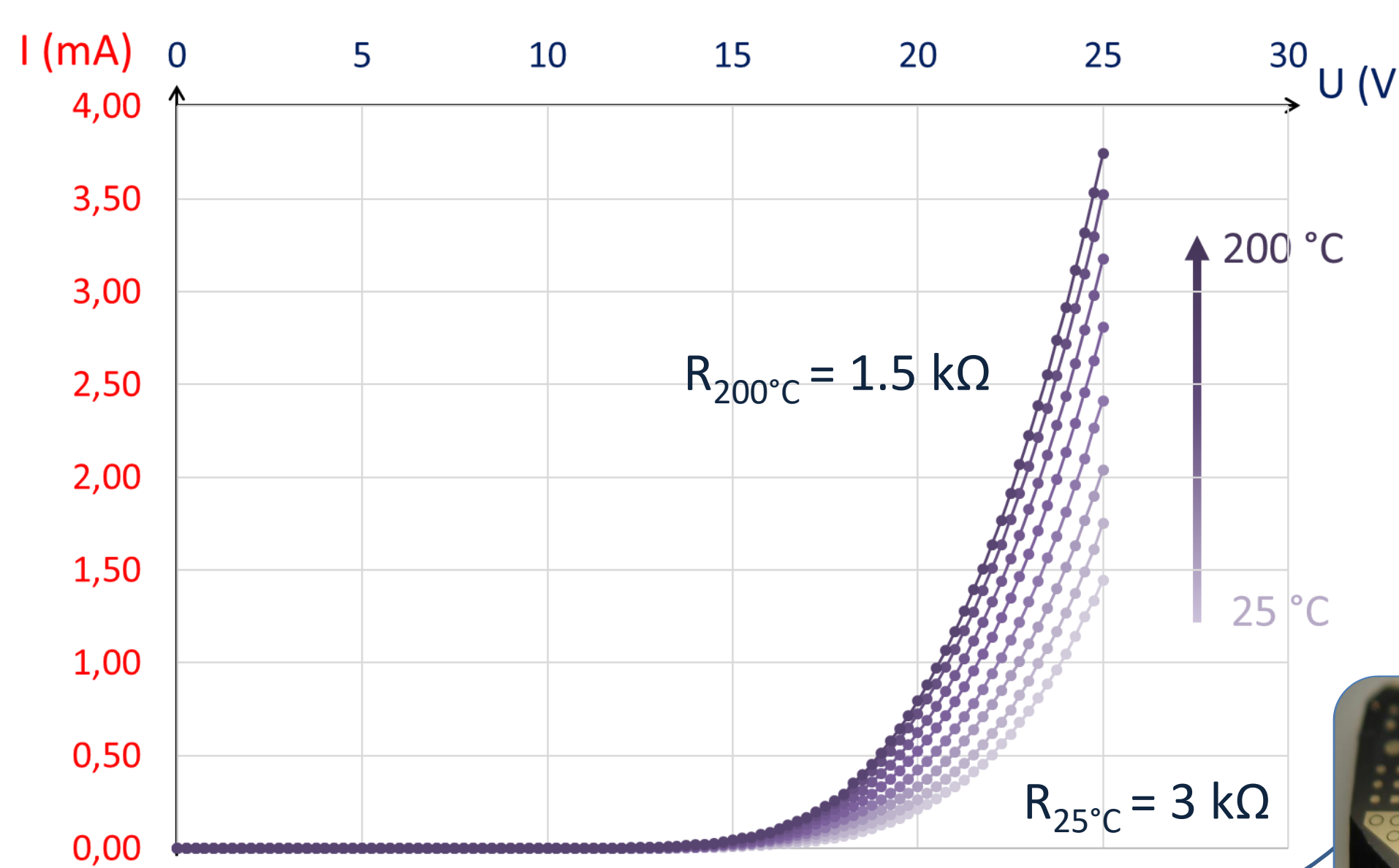


➤ Forward current @ different temperatures for a 200 μm square diode

- Low variation with temperature
- 10 A/cm² @ 200 °C

➤ Characterizations in progress

- C(V) & OBIC measurements
- High temperature measurements (T = 600 °C)



Conclusion

- ✓ A large freestanding (100) P⁺ diamond substrate (4.6 x 4.6 mm²)
 - ✓ A highly doped N⁺ layer growth (2.5×10^{19} at/cm³)
 - ✓ First vertical PIN (100) diode layers fully grown by MPCVD
 - ✓ Vertical PIN diode functionality is demonstrated: current flowing with on and off states
- To be addressed...*
- TCAD simulations of the PIN diode behaviour
 - Complementary electrical characterizations (TLM, OBIC, C(V))

This work is supported by the French national nanofabrication network Renatech and by the LAAS characterization platform PROOF